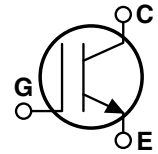
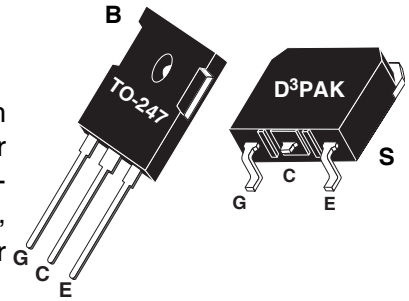


### POWER MOS 7® IGBT

A new generation of high voltage power IGBTs. Using punch-through technology and a proprietary metal gate, this IGBT has been optimized for very fast switching, making it ideal for high frequency, high voltage switch-mode power supplies and tail current sensitive applications. In many cases, the POWER MOS 7® IGBT provides a lower cost alternative to a Power MOSFET.



- Low Conduction Loss
- Low Gate Charge
- Ultrafast Tail Current shutoff
- 100 kHz operation @ 400V, 37A
- 200 kHz operation @ 400V, 24A
- SSOA rated

#### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT30GP60B_S	UNIT
$V_{CES}$	Collector-Emitter Voltage	600	Volts
$V_{GE}$	Gate-Emitter Voltage	$\pm 20$	
$V_{GEM}$	Gate-Emitter Voltage Transient	$\pm 30$	
$I_{C1}$	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	100	Amps
$I_{C2}$	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	49	
$I_{CM}$	Pulsed Collector Current <sup>①</sup> @ $T_C = 25^\circ\text{C}$	120	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	120A @ 600V	
$P_D$	Total Power Dissipation	463	Watts
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 250\mu\text{A}$ )	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 1\text{mA}, T_J = 25^\circ\text{C}$ )	3	4.5	6	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 30A, T_J = 25^\circ\text{C}$ )		2.2	2.7	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 30A, T_J = 125^\circ\text{C}$ )		2.1		
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_J = 25^\circ\text{C}$ ) <sup>②</sup>			250	$\mu\text{A}$
	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_J = 125^\circ\text{C}$ ) <sup>②</sup>			2500	
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V$ )			$\pm 100$	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## DYNAMIC CHARACTERISTICS

APT30GP60B\_S

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
$C_{ies}$	Input Capacitance	<b>Capacitance</b> $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		3200		pF	
$C_{oes}$	Output Capacitance			295			
$C_{res}$	Reverse Transfer Capacitance			20			
$V_{GEP}$	Gate-to-Emitter Plateau Voltage	<b>Gate Charge</b> $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 30A$		7.5		V	
$Q_g$	Total Gate Charge <sup>③</sup>			90		nC	
$Q_{ge}$	Gate-Emitter Charge			20			
$Q_{gc}$	Gate-Collector ("Miller") Charge			30			
SSOA	Switching SOA	$T_J = 150^\circ\text{C}, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 600V$	120			A	
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (25°C)</b> $V_{CC}(\text{Peak}) = 400V$ $V_{GE} = 15V$ $I_C = 30A$ $R_G = 5\Omega$ $T_J = +25^\circ\text{C}$		13		ns	
$t_r$	Current Rise Time			18			
$t_{d(off)}$	Turn-off Delay Time			55			
$t_f$	Current Fall Time			46			
$E_{on1}$	Turn-on Switching Energy <sup>④</sup>				260		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>⑤</sup>				335		
$E_{off}$	Turn-off Switching Energy <sup>⑥</sup>				250	330	
$t_{d(on)}$	Turn-on Delay Time		<b>Inductive Switching (125°C)</b> $V_{CC}(\text{Peak}) = 400V$ $V_{GE} = 15V$ $I_C = 30A$ $R_G = 5\Omega$ $T_J = +125^\circ\text{C}$		13		ns
$t_r$	Current Rise Time			18			
$t_{d(off)}$	Turn-off Delay Time			84			
$t_f$	Current Fall Time			80			
$E_{on1}$	Turn-on Switching Energy <sup>④</sup>				260		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>⑤</sup>				508		
$E_{off}$	Turn-off Switching Energy <sup>⑥</sup>				518	750	

## THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.27	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case (DIODE)			N/A	
$W_T$	Package Weight			5.90	gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices,  $I_{ces}$  includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④  $E_{on1}$  is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)

⑤  $E_{on2}$  is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

APT Reserves the right to change, without notice, the specifications and information contained herein.

# TYPICAL PERFORMANCE CURVES

APT30GP60B

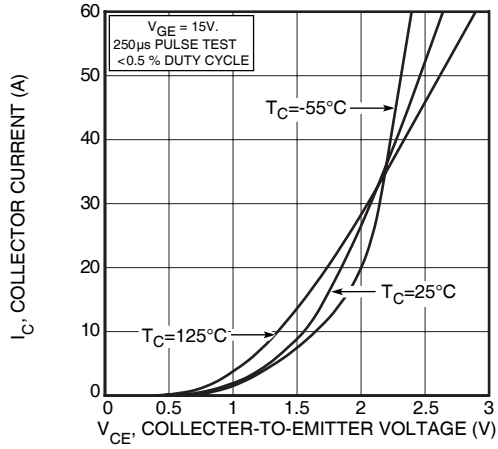


FIGURE 1, Output Characteristics ( $V_{GE} = 15V$ )

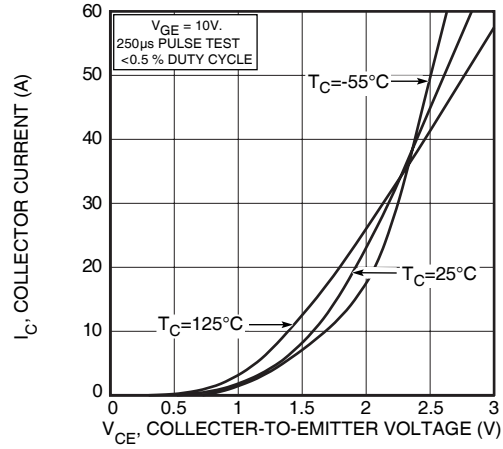


FIGURE 2, Output Characteristics ( $V_{GE} = 10V$ )

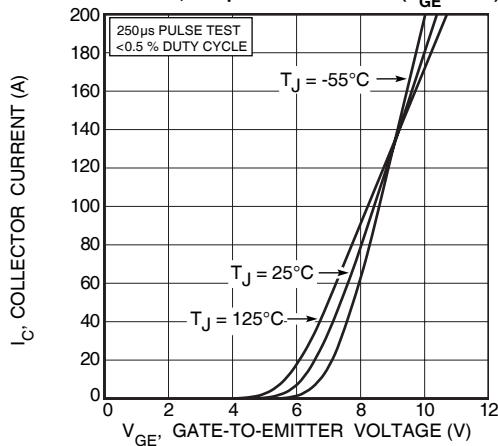


FIGURE 3, Transfer Characteristics

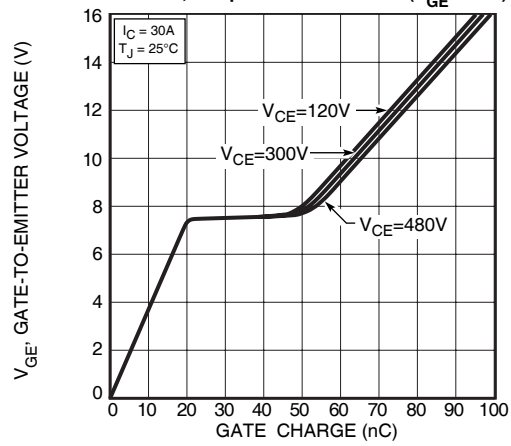


FIGURE 4, Gate Charge

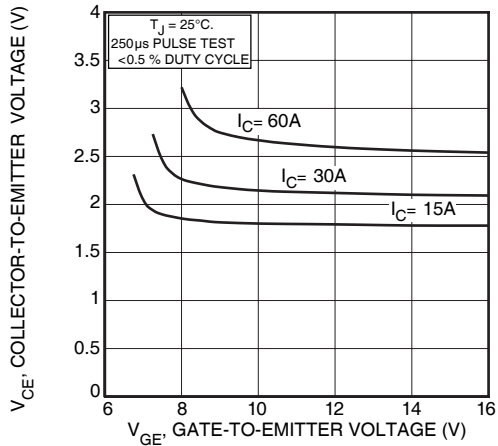


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

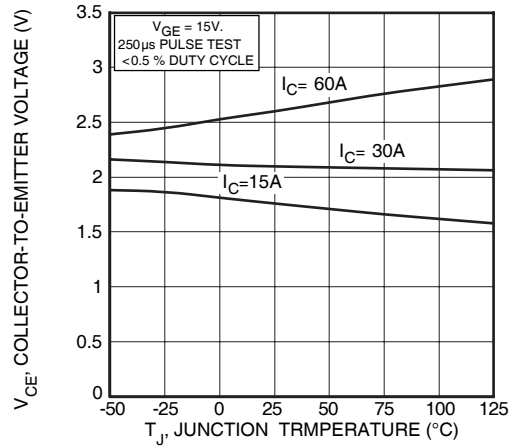


FIGURE 6, On State Voltage vs Junction Temperature

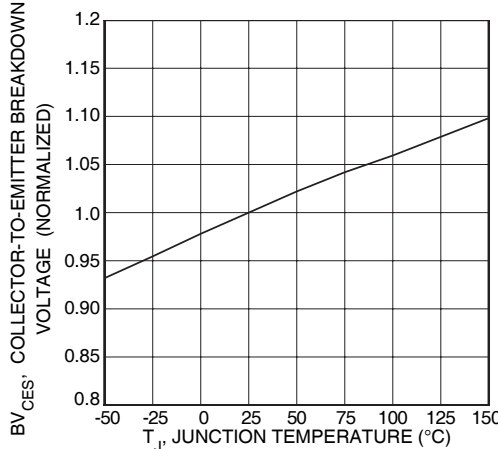


FIGURE 7, Breakdown Voltage vs. Junction Temperature

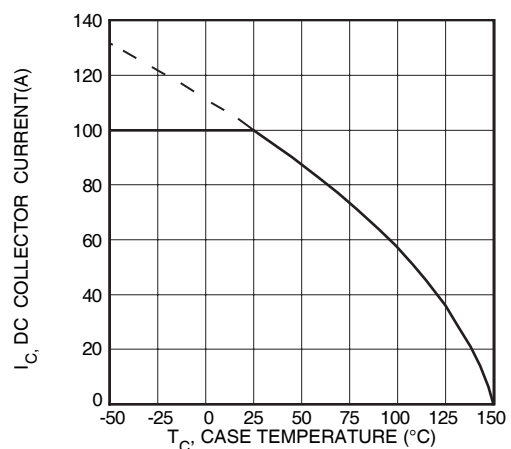


FIGURE 8, DC Collector Current vs Case Temperature

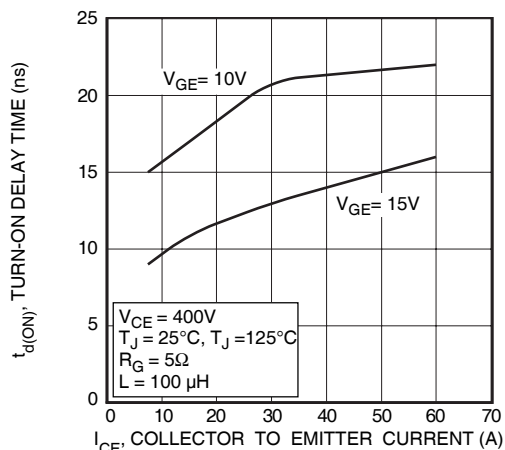


FIGURE 9, Turn-On Delay Time vs Collector Current

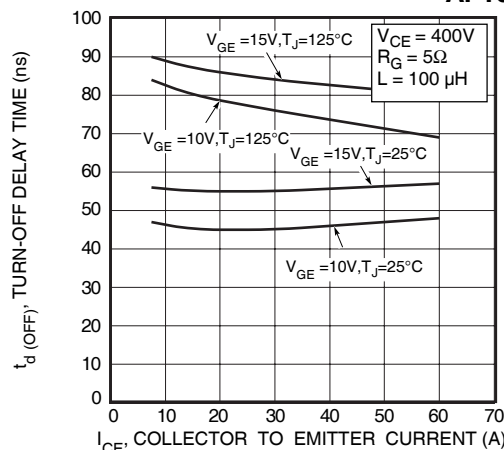


FIGURE 10, Turn-Off Delay Time vs Collector Current

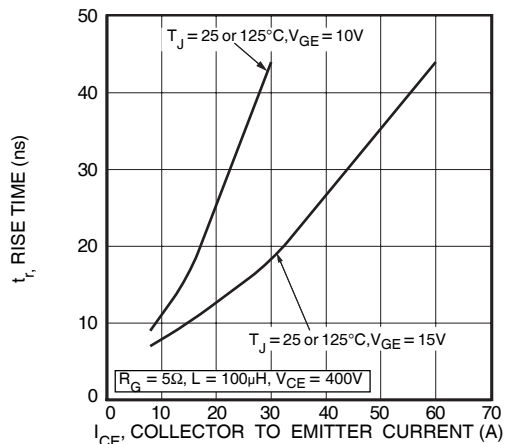


FIGURE 11, Current Rise Time vs Collector Current

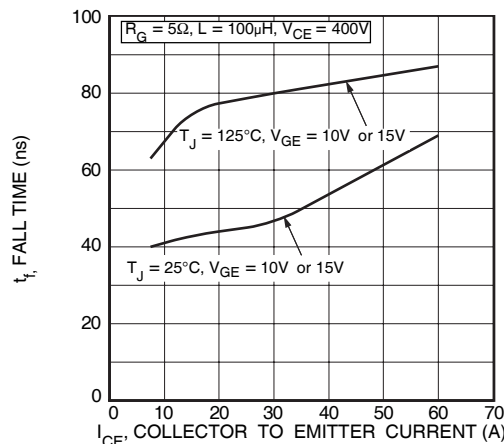


FIGURE 12, Current Fall Time vs Collector Current

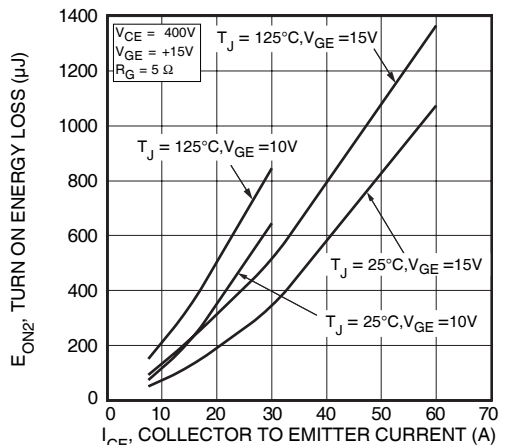


FIGURE 13, Turn-On Energy Loss vs Collector Current

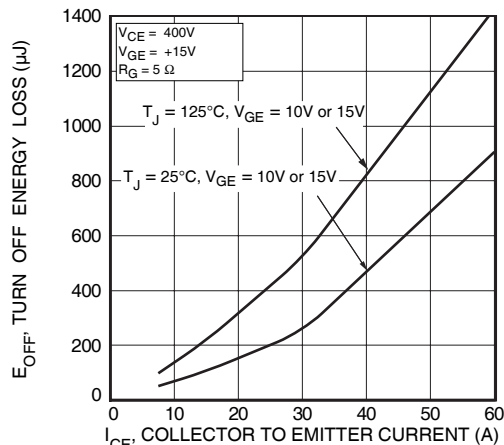


FIGURE 14, Turn Off Energy Loss vs Collector Current

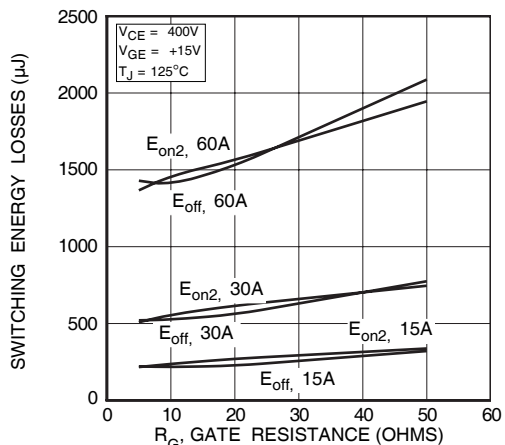


FIGURE 15, Switching Energy Losses vs. Gate Resistance

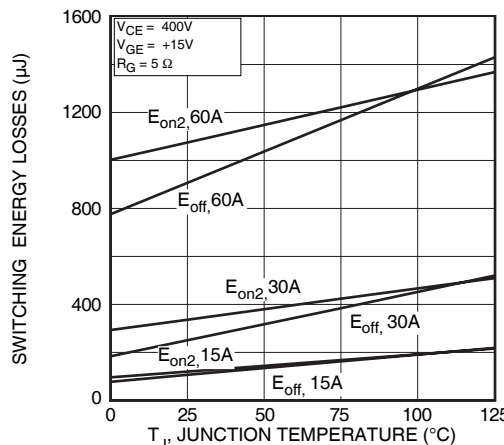


FIGURE 16, Switching Energy Losses vs Junction Temperature

# TYPICAL PERFORMANCE CURVES

APT30GP60B

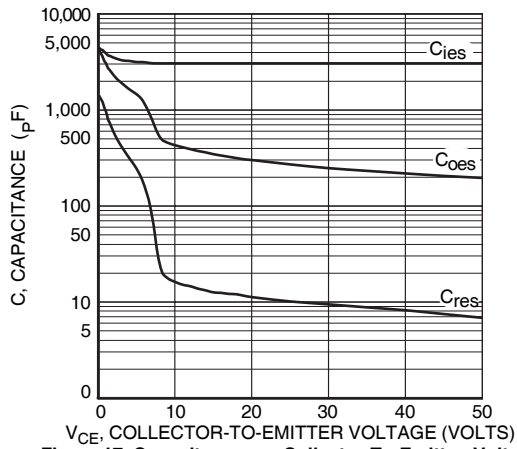


Figure 17, Capacitance vs Collector-To-Emitter Voltage

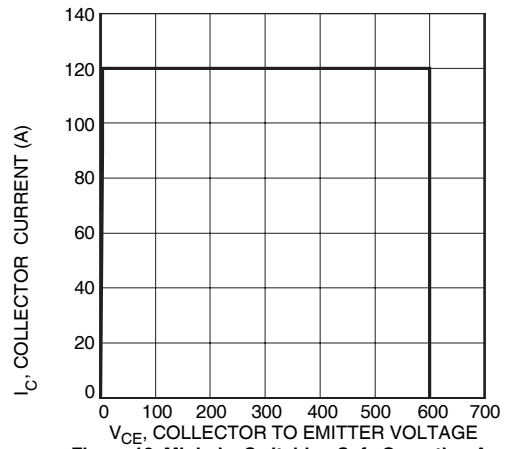


Figure 18, Minimum Switching Safe Operating Area

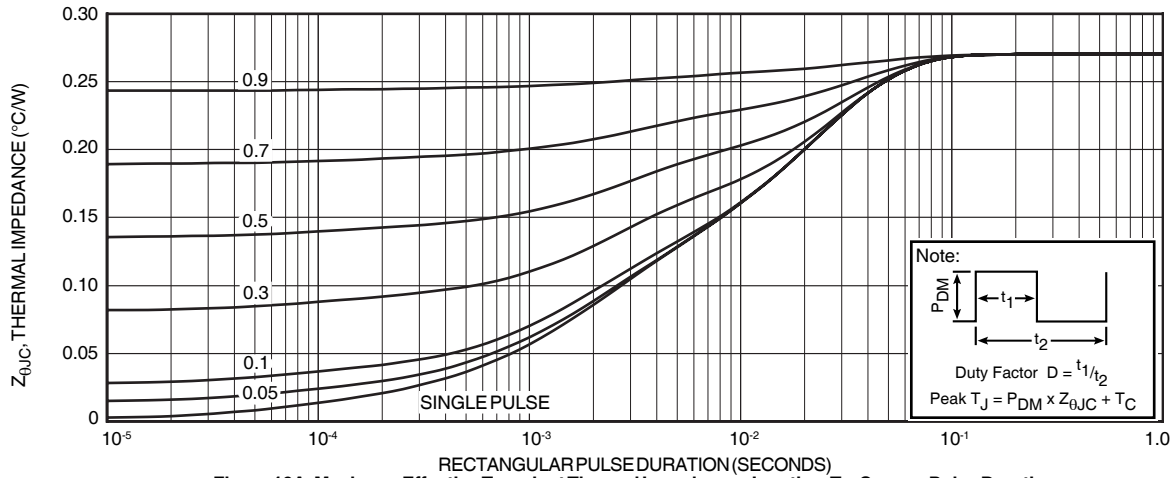


Figure 19A, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

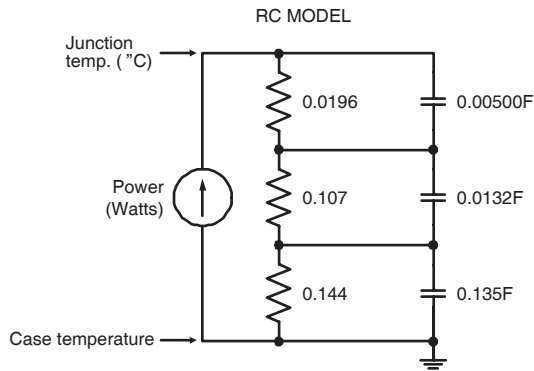


FIGURE 19B, TRANSIENT THERMAL IMPEDANCE MODEL

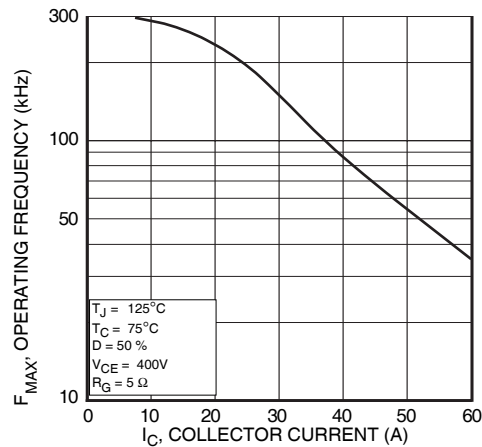


Figure 20, Operating Frequency vs Collector Current

$$F_{max} = \min(f_{max1}, f_{max2})$$

$$f_{max1} = \frac{0.05}{t_{d(on)} + t_r + t_{d(off)} + t_f}$$

$$f_{max2} = \frac{P_{diss} - P_{cond}}{E_{on2} + E_{off}}$$

$$P_{diss} = \frac{T_J - T_C}{R_{\theta JC}}$$